

低消費電力SRAM 発注型名

R1 L V 5256 E SA - 5 S I #B1

R1 L P 04 08 D SP - 5 S I #B0

RM L V 04 16 E G SB - 4 S 2 #A A 1

RENESAS Memory

Chip configuration

L	LPSRAM, Single chip
W	LPSRAM, Two chips

Operating Voltage

V	3V
P	5V

Memory Density

5256	256Kb (x8)
01	1Mb
02	2Mb
04	4Mb
08	8Mb
16	16Mb
32	32Mb
64	64Mb

Bus Width

08	x8
16	x16

Chip Generation

Industrial Grade

Package Type

SA	TSOP-I (256Kb/8Mb/16Mb/32Mb/64Mb) sTSOP (1Mb/2Mb/4Mb)
SB	TSOP-II
SD	μTSOP
SF	TSOP-I (1Mb)
SP	SOP (256Kb, 4Mb)
SN	SOP (1Mb)
BG	FBGA

Packing, Environmental

	Packing	Environmental
#B0 / #B1	Tray or Magazine	Pb free
#S0 / #S1	Tape & Reel	Pb free

Assembly Site Rev. , etc.

Environment

A	Pb free (pure-Tin plating)
C	Pb free (non pure-Tin plating)

0	Rev. Code
1	Rev. Code

Packing

A	Tray
C	Magazine
H	Tape & Reel (TSOP, uTSOP, SOP)
K	Tape & Reel (FBGA, sTSOP)

Operating Temperature

R	0 to 70 deg. C
I	-40 to 85 deg. C
2	-40 to 85 deg. C

Stand-by current / Data retention current

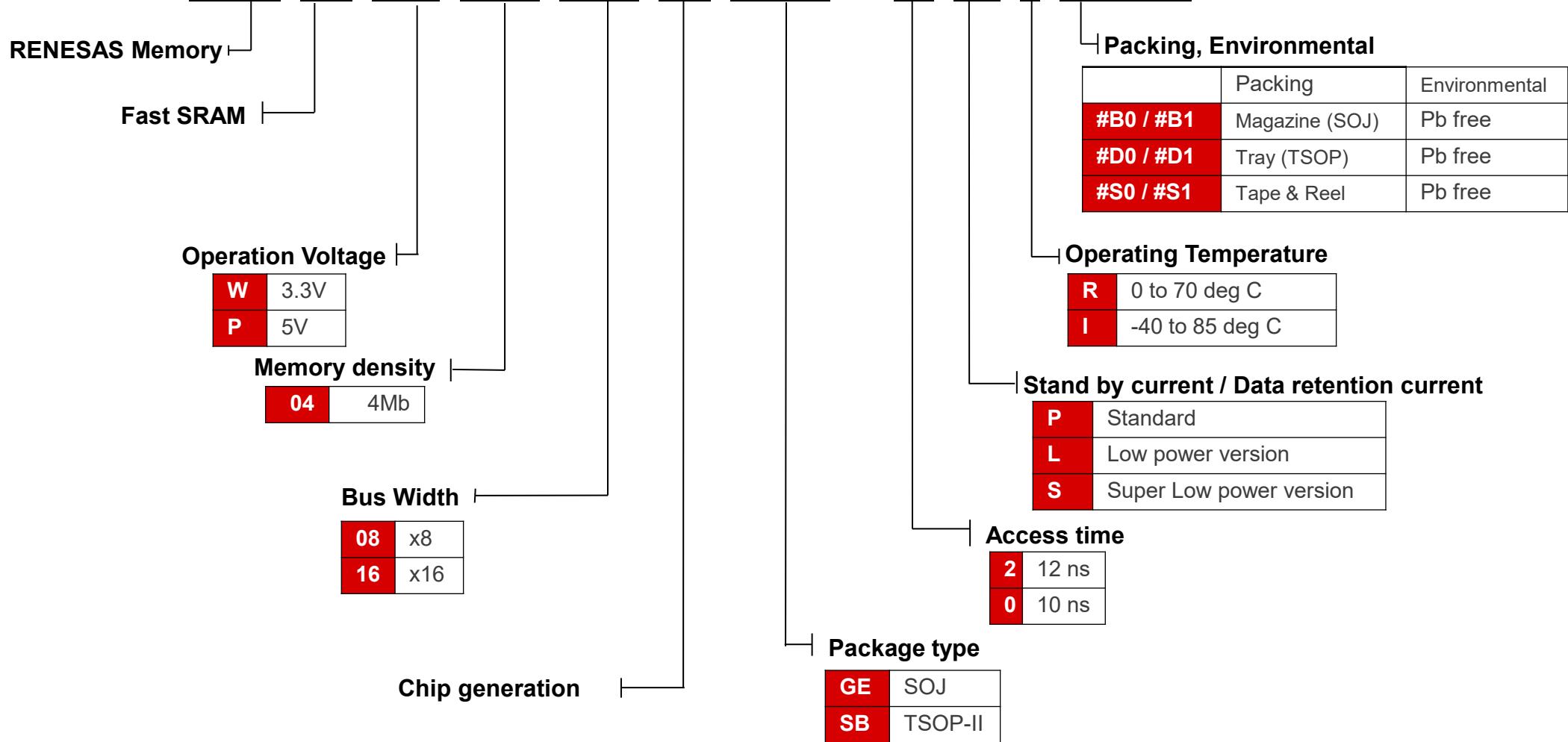
L	Standard
S	Low power version

Access time

5	55 ns
4	45 ns

高速 4Mb SRAM 発注型名

R1 R W 04 16 D SB - 2 P I #D1



Example shown here: Part number R1RW0416DSB-2PI#D1